

Features

- $V_{DS} = 20V, I_D = 0.8A$
- $R_{DS(ON)} < 250m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 300m\Omega @ V_{GS}=2.5V$
- ESD Protection

Application

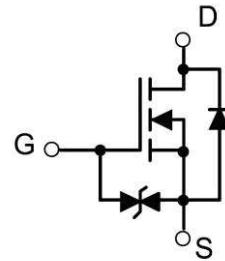
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration

Circuit diagram



SOT-523



Marking: A

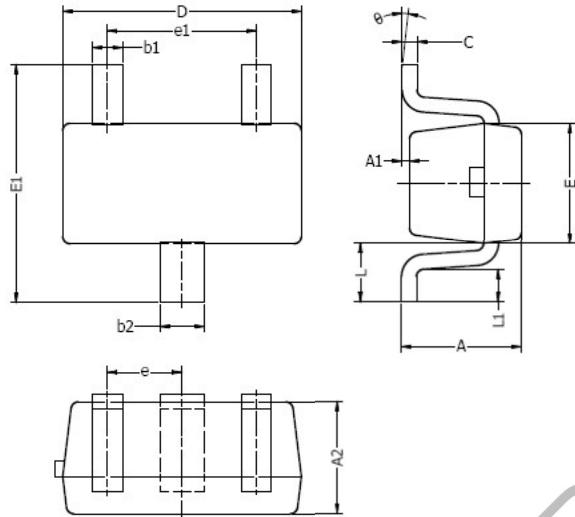
Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	0.8	A
Pulsed Drain Current ($t=300\mu s$) ⁽¹⁾	I_{DM}	1.8	A
Power Dissipation ⁽²⁾	P_D	280	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	452	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 8\text{V}, V_{\text{DS}} = 0\text{V}$			± 10	μA
Gate threshold voltage ⁽³⁾	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	0.5	0.75	1.1	V
Drain-source on-resistance ⁽³⁾	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 550\text{mA}$		180	250	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_D = 450\text{mA}$		230	300	
Forward transconductance	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_D = 500\text{mA}$		1.7		S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$			120	pF
Output Capacitance	C_{oss}				20	
Reverse Transfer Capacitance	C_{rss}				15	
Switching Characteristics⁽⁴⁾						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, I_D = 500\text{mA}, V_{\text{GS}} = 4.5\text{V}, R_G = 10\Omega$		6.7		ns
Turn-on rise time	t_r			4.8		
Turn-off delay time	$t_{\text{d}(\text{off})}$			17.3		
Turn-off fall time	t_f			7.4		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$I_S = 0.15\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V

SOT523 Package Outline Drawing



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

